DISCRETE SEMICONDUCTORS

DATA SHEET

PEMD13; **PUMD13** NPN/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

Product specification Supersedes data of 2001 Feb 27 2003 Oct 08





NPN/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

PEMD13; PUMD13

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- . Control of IC inputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	_	50	V
I _O	output current (DC)	_	100	mA
TR1	NPN	_	_	ı
TR2	PNP	_	_	-
R1	bias resistor	4.7	-	kΩ
R2	bias resistor	47	_	kΩ

DESCRIPTION

NPN/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE	PACKAGE		MARKING CODE	PNP/PNP	NPN/NPN
NUMBER	PHILIPS	EIAJ	WARKING CODE	COMPLEMENT	COMPLEMENT
PEMD13	SOT666		Z1	PEMB13	PEMH13
PUMD13	SOT363	SC-88	3*1 ⁽¹⁾	PUMB13	PUMH13

Note

- * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
I TPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION	
PEMD13	6 5 4	1	emitter TR1	
PUMD13		2	base TR1	
	R1 R2	3	collector TR2	
	TR2	4	emitter TR2	
		5	base TR2	
	│	6	collector TR1	
	1 2 3			
	1 2 3 Top view MAM468			

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ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
TIPE NUMBER	NAME	DESCRIPTION	VERSION
PEMD13	_	plastic surface mounted package; 6 leads	SOT666
PUMD13	_	plastic surface mounted package; 6 leads	SOT363

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT				
Per transist	Per transistor; for the PNP transistor with negative polarity							
V _{CBO}	collector-base voltage open emitter		_	50	V			
V _{CEO}	collector-emitter voltage	open base	_	50	V			
V _{EBO}	emitter-base voltage	open collector	_	10	V			
VI	input voltage TR1							
	positive		_	+30	V			
	negative		_	-5	V			
V _I	input voltage TR2							
	positive		_	+5	V			
	negative		_	-30	V			
Io	output current (DC)		_	100	mA			
I _{CM}	peak collector current		_	100	mA			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C						
	SOT363	note 1	_	200	mW			
	SOT666	notes 1 and 2	_	200	mW			
T _{stg}	storage temperature		-65	+150	°C			
Tj	junction temperature		_	150	°C			
T _{amb}	operating ambient temperature		-65	+150	°C			
Per device								
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C						
	SOT363	note 1	_	300	mW			
	SOT666	notes 1 and 2	_	300	mW			

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	stor; for the PNP transistor with ne					
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0	_	_	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0	_	_	1	μΑ
		V _{CE} = 30 V; I _B = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	170	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 mA	100	_	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 5 mA; I _B = 0.25 mA	_	-	100	mV
V _{i(off)}	input-off voltage	$I_C = 100 \mu A; V_{CE} = 5 V$	_	0.6	0.5	V
V _{i(on)}	input-on voltage	$I_C = 5 \text{ mA}; V_{CE} = 0.3 \text{ V}$	1.3	0.9	_	V
R1	input resistor		3.3	4.7	6.1	kΩ
R2 R1	resistor ratio		8	10	12	
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz				
	TR1 (NPN)		_	-	2.5	pF
	TR2 (PNP)		_	-	3	pF

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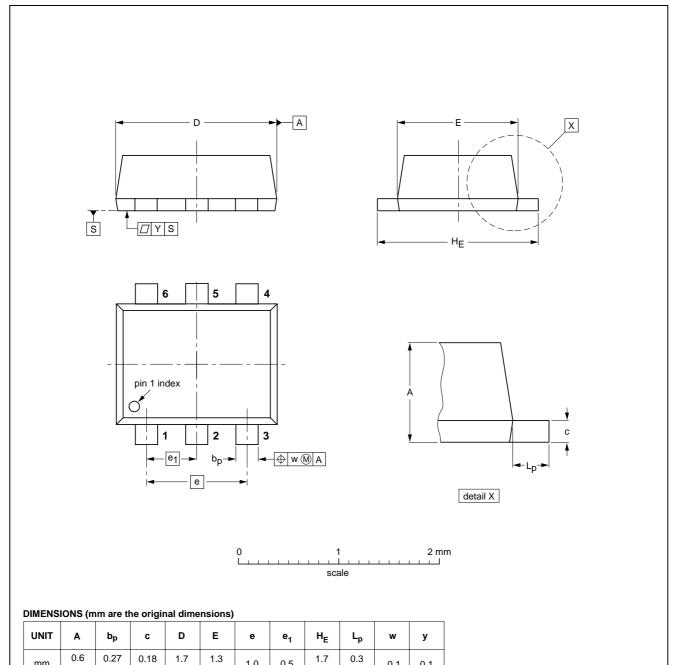
NPN/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

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PACKAGE OUTLINES

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						-01-01-04 01-08-27	

0.1

1.0

0.5

2003 Oct 08 5

mm

0.17

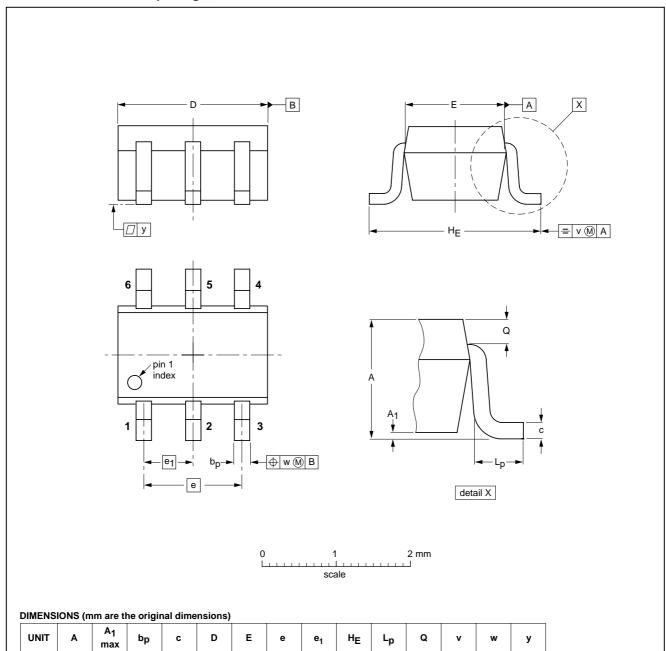
0.08

NPN/PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 47 k Ω

PEMD13; PUMD13

Plastic surface mounted package; 6 leads

SOT363



OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

0.65

1.3

0.45

0.2

0.2

0.1

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0.30

0.20

0.1

mm

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Notes

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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